

Description

The DGTD65T50S1PT is produced using advanced Field Stop Trench IGBT Technology, which provides excellent quality and high-switching performance.

Features

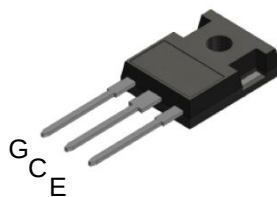
- High-Speed Switching & Low Power Loss
- $V_{CE(sat)} = 1.85V$ @ $I_C = 50A$
- High Input Impedance
- $t_{rr} = 80ns$ (typ) @ $di_F/dt = 1000A/\mu s$
- $E_{off} = 0.55mJ$ @ $T_C = 25^\circ C$
- Maximum Junction Temperature $175^\circ C$
- **Lead-Free Finish & RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Applications

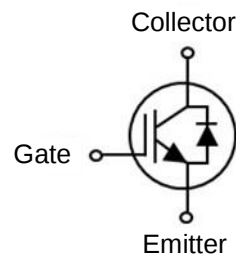
- UPS
- Welder
- Solar Inverter
- IH Cooker

Mechanical Data

- Case: TO-247 (Type MC)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Terminals: Finish – Matte Tin Plated Leads.
Solderable per MIL-STD-202, Method 208 
- Weight: 5.6 grams (Approximate)



TO-247



Device Symbol

Ordering Information (Note 4)

Product	Marking	Quantity
DGTD65T50S1PT	DGTD65T50S1	450 per Box in Tubes (Note 5)

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.
 5. 30 Devices per Tube.

Marking Information



D = Manufacturer's Marking
 DGTD65T50S1 = Product Type Marking Code
 YY = Year (ex: 18 = 2018)
 LLLLL = Lot Code
 WW = Week (01 to 53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Collector-Emitter Voltage		V _{CE}	650	V
DC Collector Current, limited by T _{vjmax}	T _C = 25°C	I _C	100	A
	T _C = 100°C		50	A
Pulsed Collector Current, t _p limited by T _{vjmax}		I _{Cpuls}	200	A
Turn Off Safe Operating Area V _{CE} ≤ 650V, T _{vj} = 175°C		-	200	A
Diode Forward Current limited by T _{vjmax}	T _C = 25°C	I _F	60	A
	T _C = 100°C		30	A
Diode Pulsed Current, t _p limited by T _{vjmax}		I _{Fpuls}	200	A
Gate-Emitter Voltage		V _{GE}	±20	V
Short Circuit Withstand Time V _{CC} ≤ 400V, V _{GE} = 15V, T _{vj} = 150°C Allowed Number of Short Circuits < 1000 Time Between Short Circuits ≥ 1.0s		tsc	5	μs

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 6)	T _C = 25°C	P _D	375	W
	T _C = 100°C		188	
Thermal Resistance, Junction to Ambient (Note 6)		R _{θJA}	40	°C/W
Thermal Resistance, Junction to Case for IGBT (Note 6)		R _{θJC}	0.40	
Thermal Resistance, Junction to Case for Diode (Note 6)		R _{θJC}	1.20	
Operating Temperature		T _{vj}	-40 to +175	°C
Storage Temperature Range		T _{STG}	-55 to +150	

Note: 6. When mounted on a standard JEDEC 2-layer FR-4 board.

Electrical Characteristics (@T_{vj} = +25°C, unless otherwise specified.)

Parameter		Symbol	Min	Typ	Max	Unit	Condition	
STATIC CHARACTERISTICS								
Collector-Emitter Breakdown Voltage		BV _{CES}	650	–	–	V	I _C = 2mA, V _{GE} = 0V	
Collector-Emitter Saturation Voltage	T _{vj} = 25°C	V _{CE(sat)}	–	1.85	2.40	V	I _C = 50A, V _{GE} = 15V	
	T _{vj} = 175°C		–	2.20	–			
Diode Forward Voltage	T _{vj} = 25°C	V _F	–	1.65	2.05	V	V _{GE} = 0V, I _F = 30A	
	T _{vj} = 175°C		–	1.55	–			
Gate-Emitter Threshold Voltage		V _{GE(th)}	3.8	5.0	6.2	V	V _{CE} = V _{GE} , I _C = 0.5mA	
Zero Gate Voltage Collector Current		I _{CES}	–	–	40	μA	V _{CE} = 650V, V _{GE} = 0V	
Gate-Emitter Leakage Current		I _{GES}	–	–	±100	nA	V _{GE} = 20V, V _{CE} = 0V	
DYNAMIC CHARACTERISTICS								
Total Gate Charge		Q _g	–	287	–	nC	V _{CE} = 520V, I _C = 50A, V _{GE} = 15V	
Gate-Emitter Charge		Q _{ge}	–	42	–			
Gate-Collector Charge		Q _{gc}	–	181	–			
Input Capacitance		C _{ies}	–	4,453	–	pF	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	
Reverse Transfer Capacitance		C _{res}	–	161	–			
Output Capacitance		C _{oes}	–	238	–			
Internal Emitter Inductance Measured 5mm (0.197") From Case		L _E	–	13	–	nH	–	
Short Circuit Collector Current Max. 1000 Short Circuits. Time Between Short Circuits ≥ 1.0s		I _{C(SC)}	–	140	–	A	V _{GE} = 15V, V _{CC} = 400V, t _{SC} ≤ 5μs, T _{vj} = 150°C	
SWITCHING CHARACTERISTICS								
Turn-on Delay Time		t _{d(on)}	–	58	–	ns	V _{GE} = 15V, V _{CC} = 400V, I _C = 50A, R _G = 7.9Ω, Inductive Load, T _{vj} = 25°C	
Rise time		t _r	–	60	–			
Turn-off Delay Time		t _{d(off)}	–	328	–			
Fall Time		t _f	–	44	–			
Turn-on Switching Energy		E _{on}	–	0.77	–	mJ		
Turn-off Switching Energy		E _{off}	–	0.55	–			
Total Switching Energy		E _{ts}	–	1.32	–			
Reverse Recovery Time		t _{rr}	–	80	–	ns	I _F = 30A, di _F /dt = 1000A/μs, T _{vj} = 25°C	
Reverse Recovery Current		I _{rr}	–	24	–	A		
Reverse Recovery Charge		Q _{rr}	–	0.95	–	μC		
Turn-on Delay Time		t _{d(on)}	–	51	–	ns	V _{GE} = 15V, V _{CC} = 400V, I _C = 50A, R _G = 7.9Ω, Inductive Load, T _{vj} = 175°C	
Rise time		t _r	–	66	–			
Turn-off Delay Time		t _{d(off)}	–	350	–			
Fall Time		t _f	–	49	–			
Turn-on Switching Energy		E _{on}	–	1.05	–	mJ		
Turn-off Switching Energy		E _{off}	–	0.55	–			
Total Switching Energy		E _{ts}	–	1.6	–			
Reverse Recovery Time		t _{rr}	–	116	–	ns	I _F = 30A, di _F /dt = 1000A/μs, T _{vj} = 175°C	
Reverse Recovery Current		I _{rr}	–	34	–	A		
Reverse Recovery Charge		Q _{rr}	–	1.97	–	μC		

Typical Performance Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

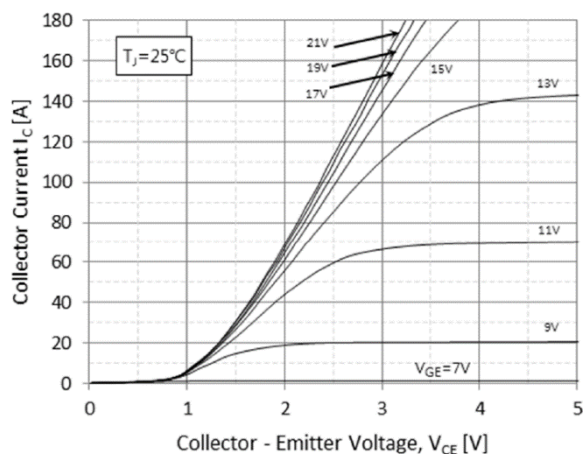


Fig.1 Typical Output Characteristics($T_J=25^\circ\text{C}$)

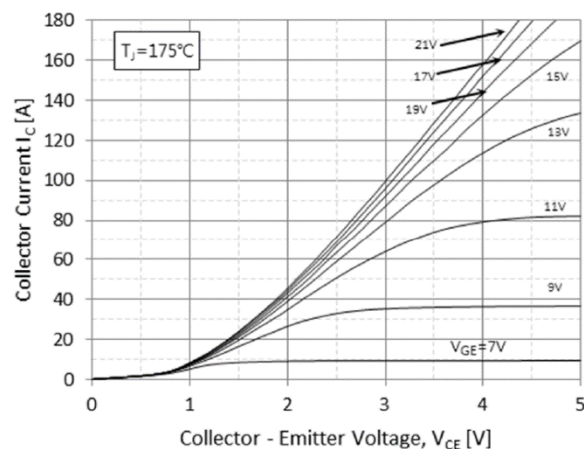


Fig.2 Typical Output Characteristics($T_J=175^\circ\text{C}$)

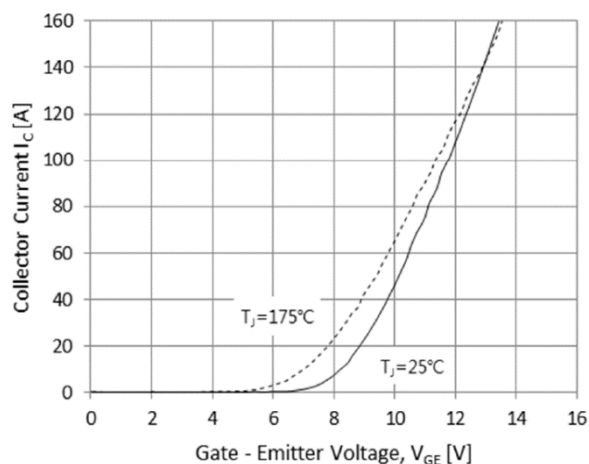


Fig.3 Typical Transfer Characteristics

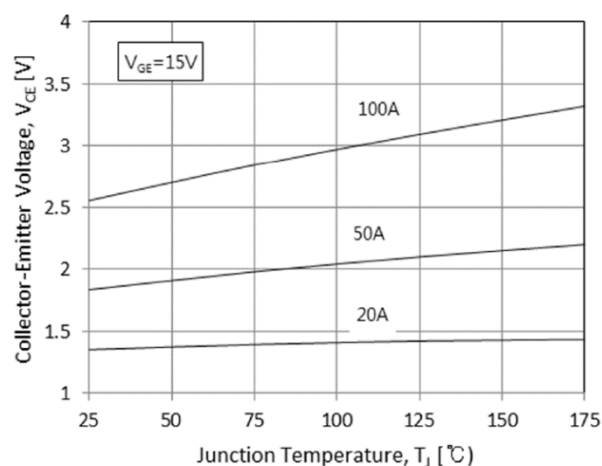


Fig.4 Typical Collector-Emitter Saturation Voltage -Junction Temperature

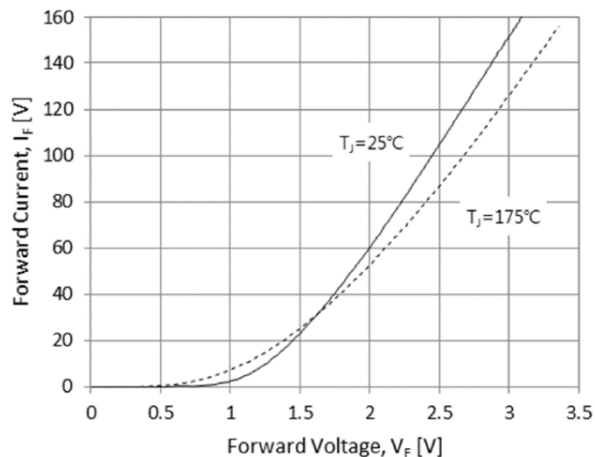


Fig.5 Diode Forward Characteristics

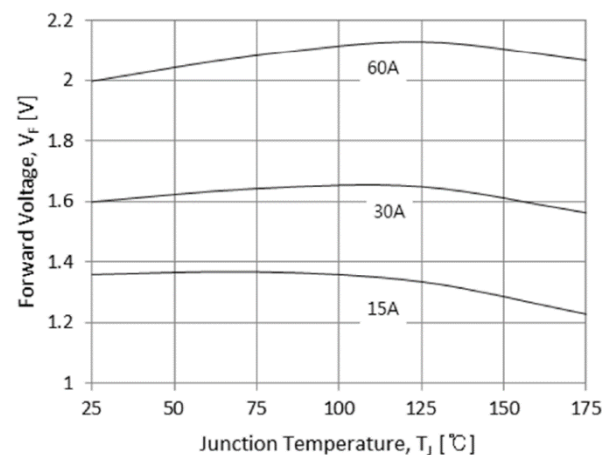


Fig.6 Diode Forward-Junction Temperature

Typical Performance Characteristics (continued)

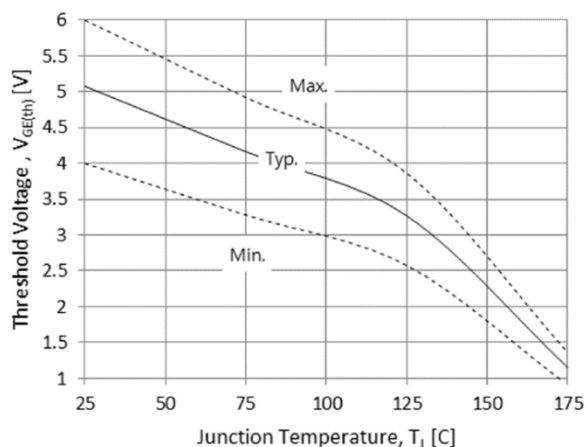


Fig.7 Threshold Voltage-Junction Temperature

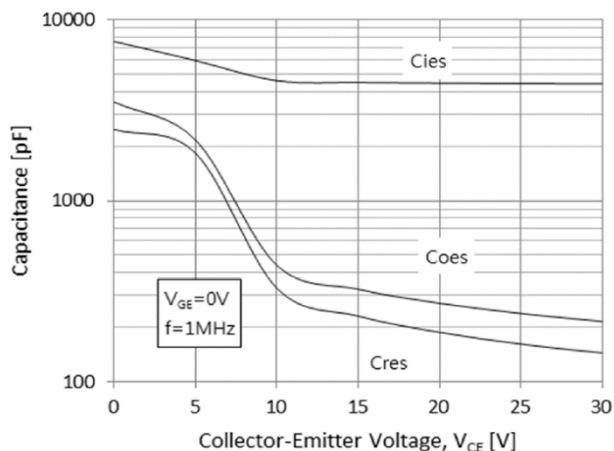


Fig.8 Typical Capacitance

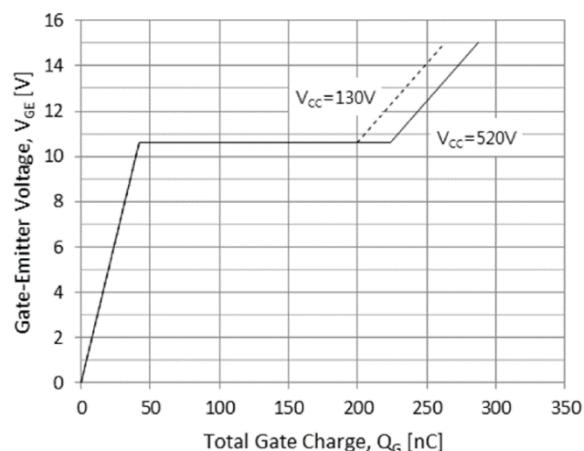


Fig.9 Typical Gate Charge

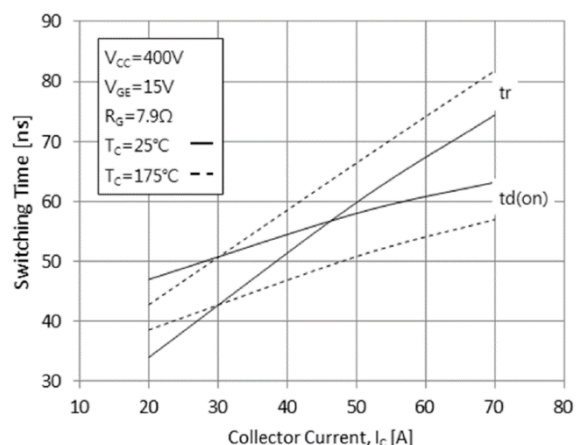


Fig.10 Typical Turn on-Collector Current

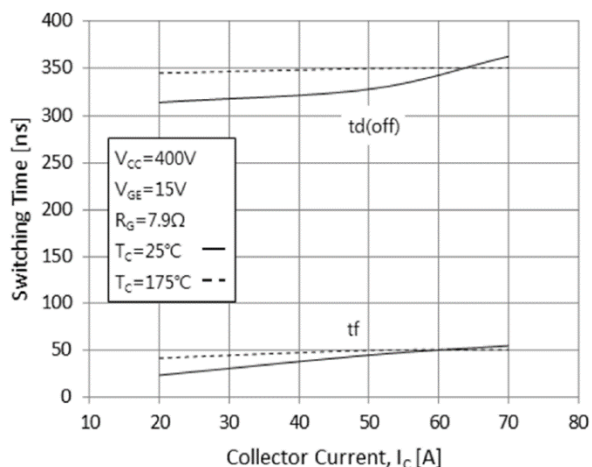


Fig.11 Typical Turn off-Collector Current

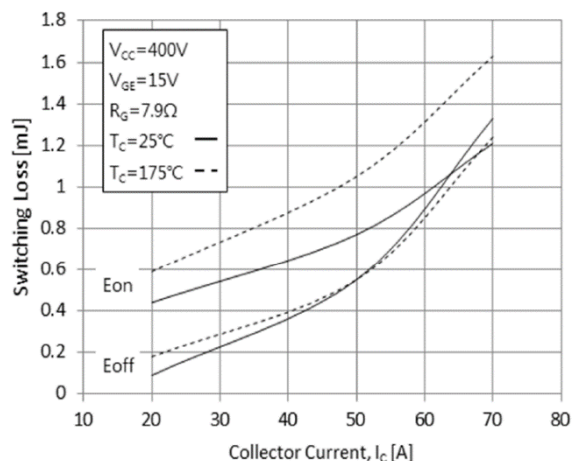


Fig.12 Switching Loss-Collector Current

Typical Performance Characteristics (cont.)

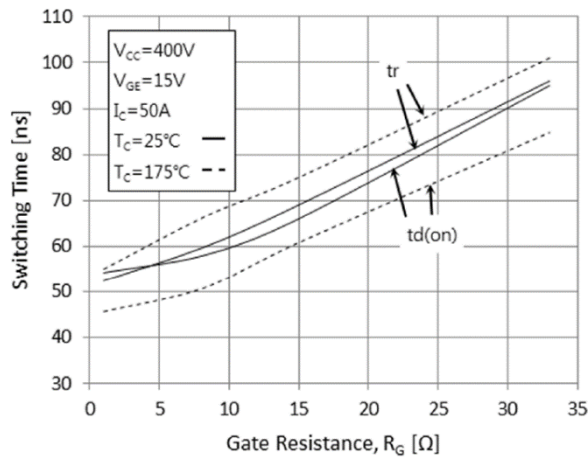


Fig.13 Turn on Characteristics-Gate Resistance

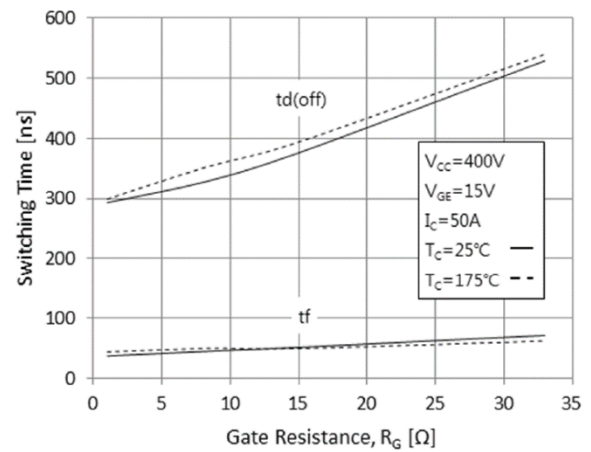


Fig.14 Turn off Characteristics-Gate Resistance

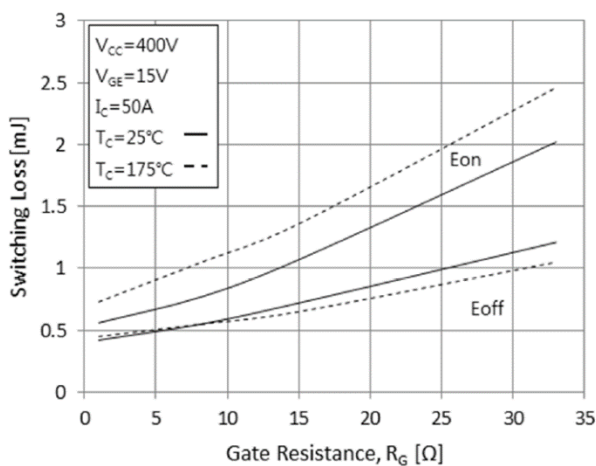


Fig.15 Switching Loss-Gate Resistance

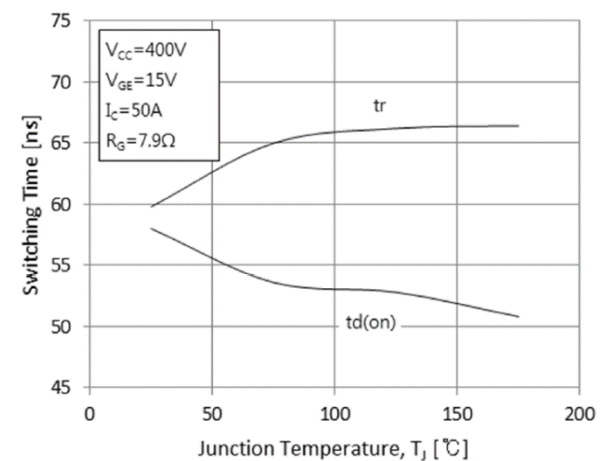


Fig.16 Turn on Characteristics-Junction Temperature

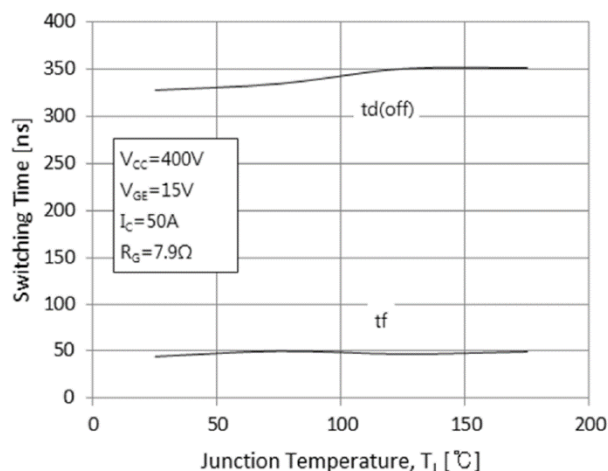


Fig.17 Turn off Characteristics-Junction Temperature

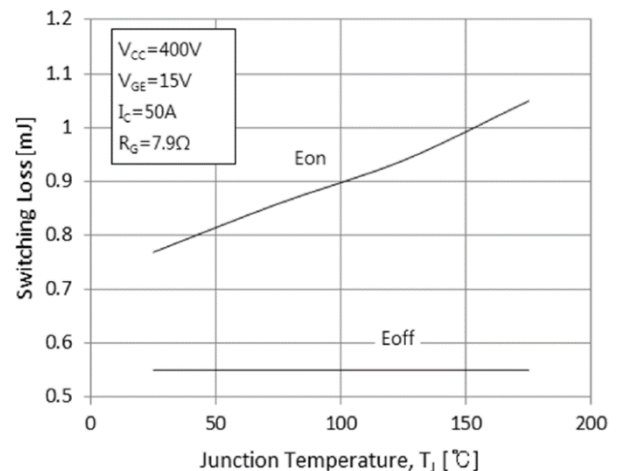


Fig.18 Switching Loss-Junction Temperature

Typical Performance Characteristics (cont.)

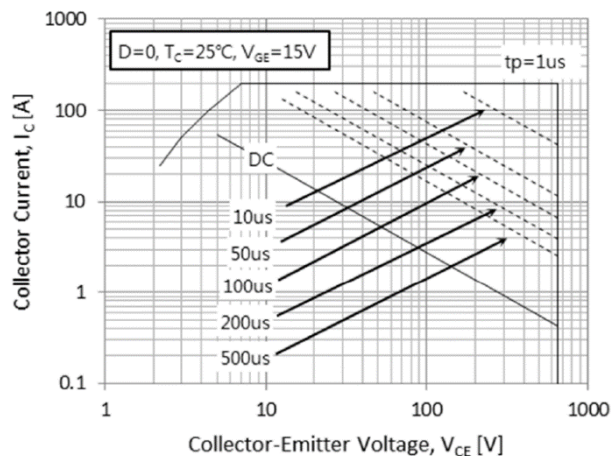


Fig.19 Forward Bias Safe Operating Area

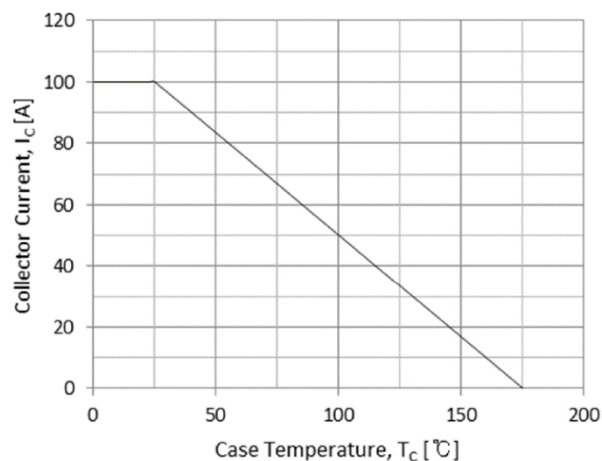


Fig.20 Case Temperature-Collector Current

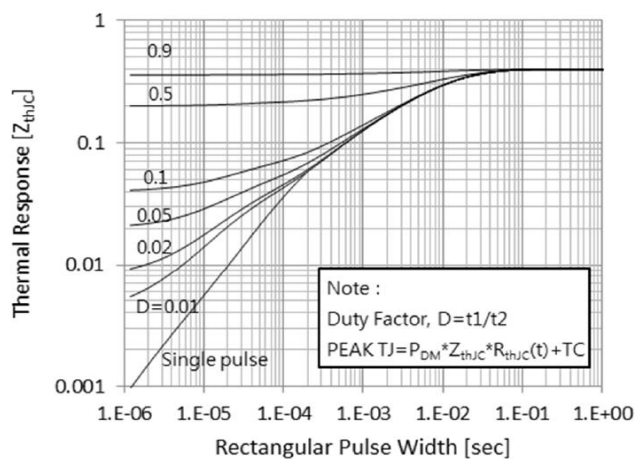


Fig.21 IGBT Transient Thermal Impedance

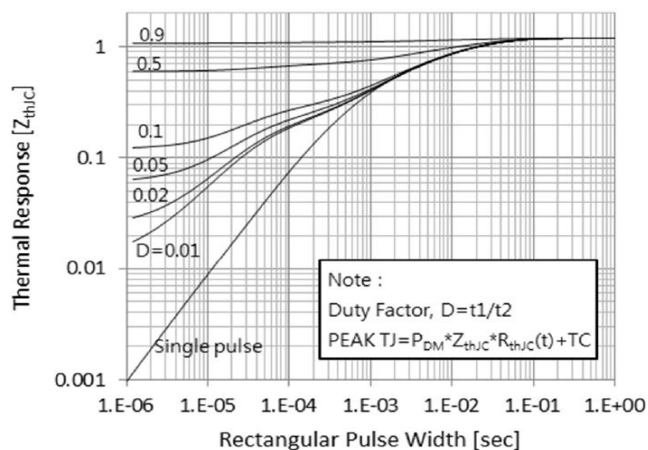
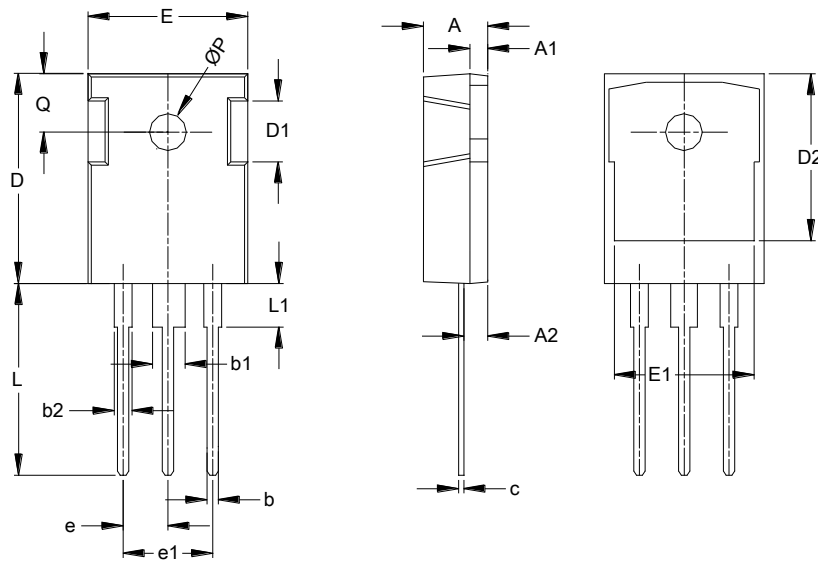


Fig.22 FRD Transient Thermal Impedance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO-247 (Type MC)



TO-247 (Type MC)			
Dim	Min	Max	Typ
A	4.700	5.310	-
A1	1.500	2.490	-
A2	2.200	2.600	-
b	0.990	1.400	-
b1	2.590	3.430	-
b2	1.650	2.390	-
c	0.380	0.890	-
D	20.30	21.46	-
D1	4.320	5.490	-
D2	13.08	-	-
E	15.45	16.26	-
E1	13.06	14.02	-
e	5.450		-
e1	10.90		-
L	19.81	20.57	-
L1	-	4.500	-
Q	5.380	6.200	-
ØP	3.500	3.700	-
All Dimensions in mm			

Note : For high-voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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